Application Serial No. 10/691,300

## **IN THE SPECIFICATION**

Please replace the paragraph beginning on page 6, line 28, with the following amended paragraph:

The T1he term "semiconductor layer" as may be used herein refers to any semiconductor material upon which and/or in which other materials may be formed. The semiconductor layer may comprise a single layer, such as, for example, the substrate 252, or it may comprise multiple layers, such as, for example, the substrate 252 and an epitaxial layer (not shown). The semiconductor wafer 250 comprises the substrate 252, with or without the epitaxial layer, and preferably includes one or more other semiconductor layers formed on the substrate. The term "wafer" is often used interchangeably with the term "silicon body," since silicon is typically employed as the semiconductor material comprising the wafer. It should be appreciated that although the present invention is illustrated herein using a portion of a semiconductor wafer, the term "wafer" may include a multiple-die wafer, a single-die wafer, or any other arrangement of semiconductor material on or in which a circuit element may be formed.